

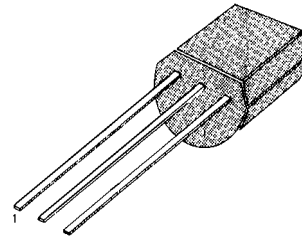
BC636/638/640**PNP EPITAXIAL SILICON TRANSISTOR****SWITCHING AND AMPLIFIER APPLICATIONS**

- Complement to BC635/637/639

ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)

Characteristic	Symbol	Rating	Unit
Collector Emitter Voltage at R _{BE} =1Kohm	V _{CER}	-45	V
		-60	V
		-100	V
Collector Emitter Voltage	V _{CES}	-45	V
		-60	V
		-100	V
Collector Emitter Voltage	V _{CEO}	-45	V
		-60	V
		-80	V
Emitter Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-1	A
Peak Collector Current	I _{CP}	-1.5	A
Base Current	I _B	-100	mA
Collector Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-65 ~ 150	°C

TO-92



1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS (T_A=25 °C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -10mA, I _B =0	-45			V
			-60			V
			-80			V
Collector Cut-off Current	I _{CBO}	V _{CB} = -30V, I _E =0			-0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μA
DC Current Gain	h _{FE}	V _{CE} = -2V, I _C = -5mA	25		250	
		V _{CE} = -2V, I _C = -150mA	40		160	
		V _{CE} = -2V, I _C = -500mA	40			
		I _C = -500mA, I _B = -50mA	25			
Collector Emitter Saturation Voltage	V _{CE (sat)}	V _{CE} = -2V, I _C = -500mA			-0.5	V
Base Emitter On Voltage	V _{BE (on)}	V _{CE} = -2V, I _C = -500mA			-1	V
Current Gain Bandwidth Product	f _T	V _{CE} = -5V, I _C = -10mA, f=50MHz		100		MHz

